TECH PUBLIC
台舟电子

TPESD4114-563

Low Capacitance TVS Diod

www.sot23.com.tw

Features

- Ultra low capacitance: 0.3pF typical (I/O to I/O)
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- Up to 4 data lines and one power line protects
- Complies with following standards:
  - – IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±25kV
  - – IEC61000-4-4 (EFT) 40A (5/50ns)
  - – IEC61000-4-5 (Lightning) 5A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

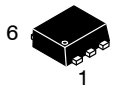
- Package: SOT-563
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below

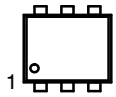
Applications

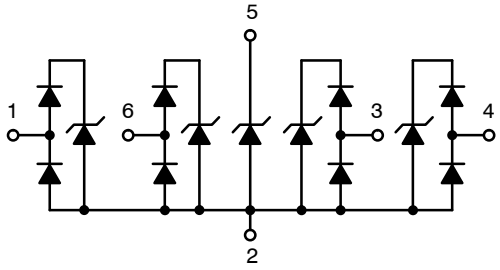
- Cellular Handsets & Accessories
- Digital Visual Interface (DVI)
- Display Port
- MDDI Ports
- USB Ports
- PCI Express
- Serial ATA

Ordering Information

Part Number	Qty per Reel	Reel Size
TPESD4114-563	4000	7″







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PROTECTION PRODUCTS

Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	120	W
Peak Pulse Current (8/20μs)	I_{PP}	5	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±25	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

ELECTRICAL CHARACTERISTICS PER LINE @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	Any I/O pin to ground
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA, any I/O pin to ground
Reverse Leakage Current	I_R			0.5	μA	V_{RWM} = 5V, any I/O pin to ground
Clamping Voltage	V_C			15	V	I_{PP} = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V_C			20	V	I_{PP} = 5A (8 x 20μs pulse), any I/O pin to ground
Junction Capacitance	C_J		0.3	0.45	pF	VR = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C_J			0.7	pF	VR = 0V, f = 1MHz, any I/O pin to ground

Characteristic Curves

Fig1. 8/20μs Pulse Waveform

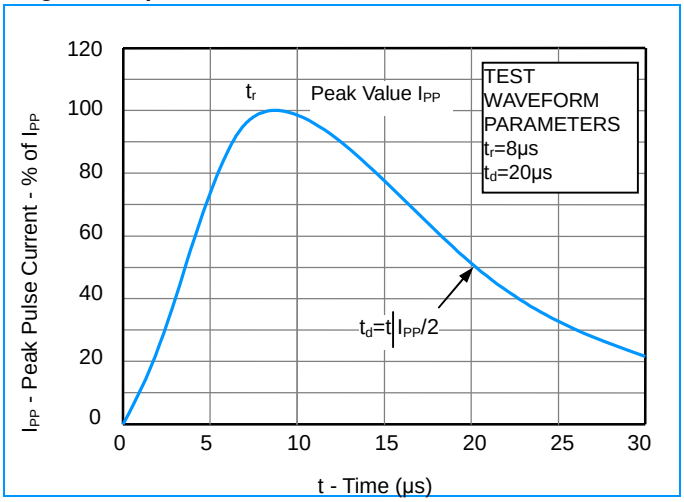


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

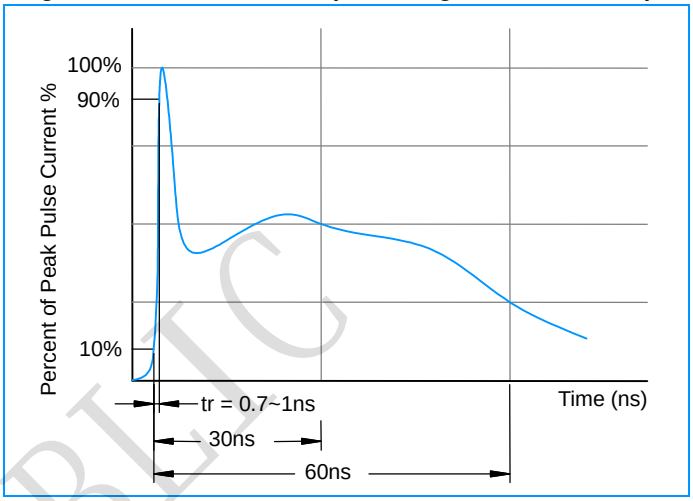


Fig3. Non - Repetitive Peak Pulse Power vs. Pulse Time

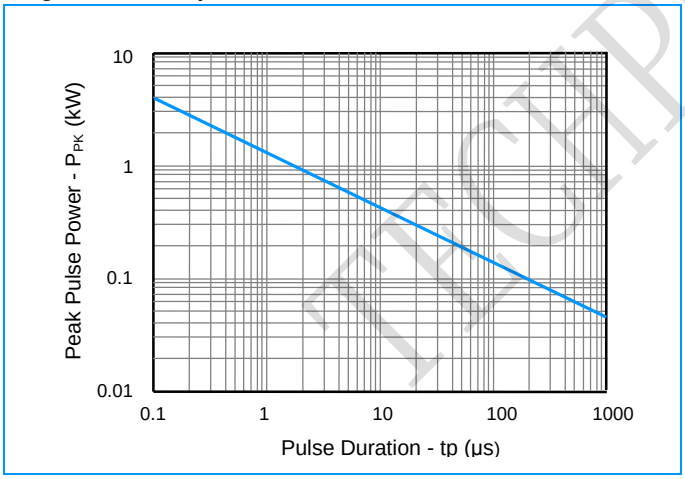
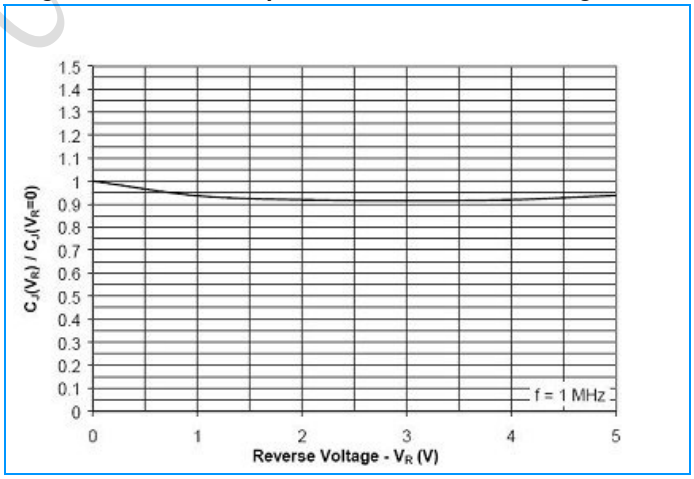
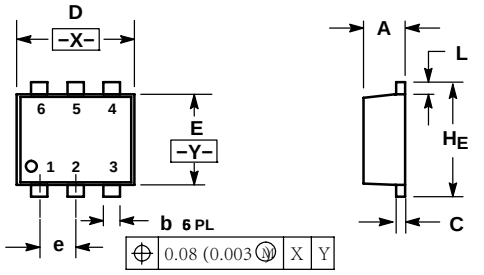


Fig4. Normalized Capacitance vs. Reverse Voltage



Outline Drawing - SOT563



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.062	0.066

Land Pattern -SOT563